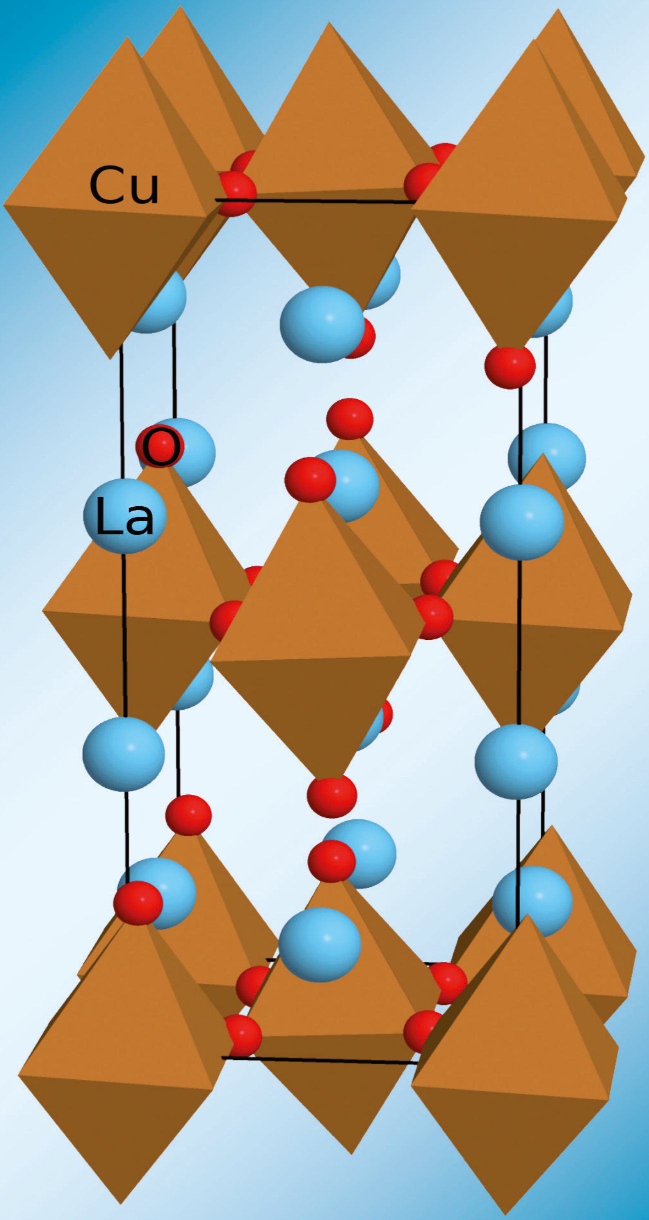

Oxygen transport in thin oxide films at high field strength

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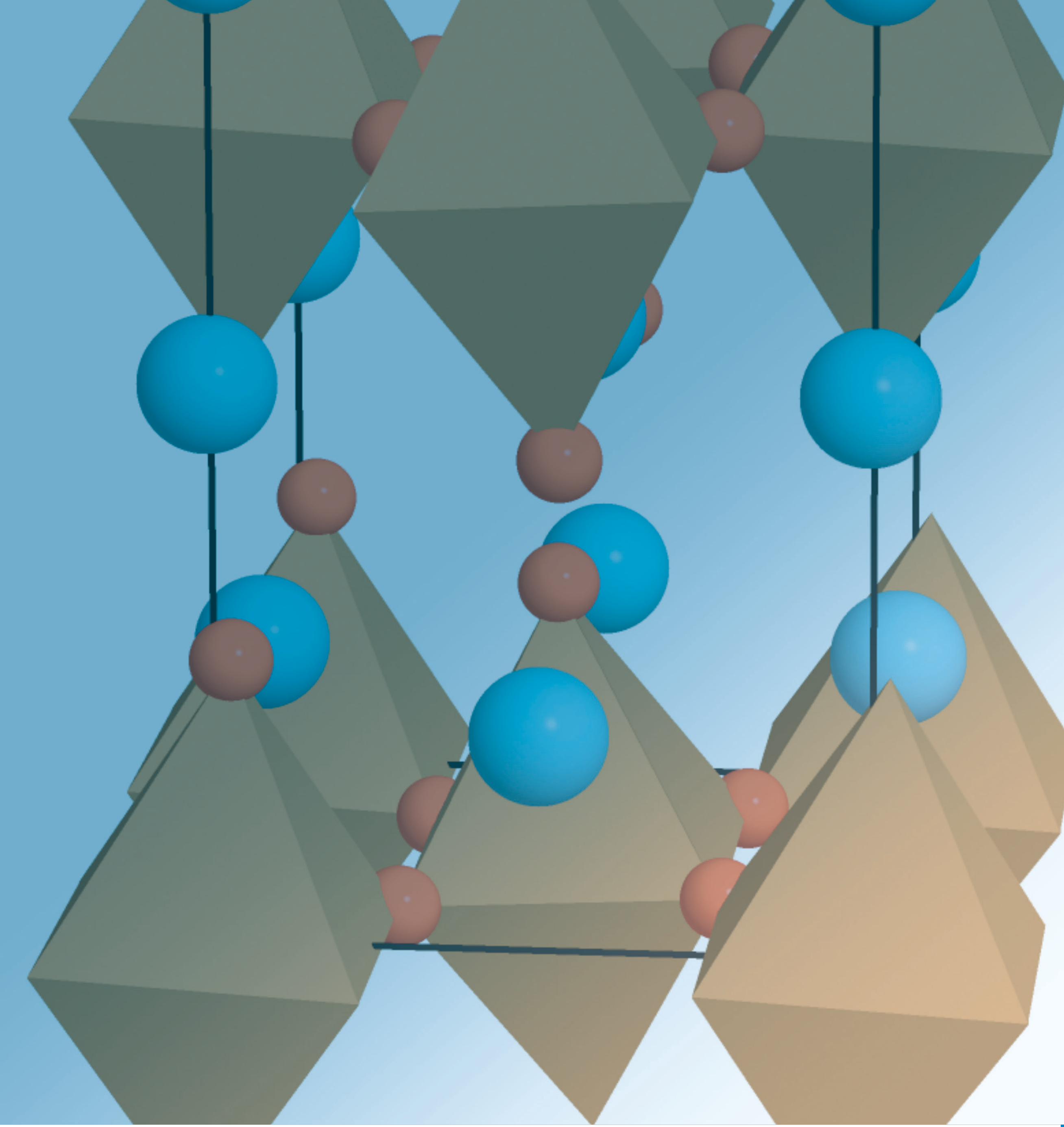

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